

# CITATION REPORT

List of articles citing

Reduction of electron tunneling current due to lateral variation of the wave function

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#	Paper	IF	Citations
47	Tunneling of Bloch electrons through vacuum barrier. <i>Europhysics Letters</i> , <b>2001</b> , 55, 404-410	1.6	23
46	Role of symmetry on interface states in magnetic tunnel junctions. <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	11
45	Ab initio theories of electric transport in solid systems with reduced dimensions. <i>Physics Reports</i> , <b>2003</b> , 377, 281-387	27.7	36
44	Bias dependence of tunneling magnetoresistance on ferromagnetic electrode thickness. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 2676-2678	3.4	4
43	Band structure, evanescent states, and transport in spin tunnel junctions. <i>Journal of Physics Condensed Matter</i> , <b>2003</b> , 15, R1603-R1639	1.8	74
42	Effects of the iron-oxide layer in Fe-FeO-MgO-Fe tunneling junctions. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	199
41	On the calculation of the magnetoresistance of tunnel junctions with parallel paths of conduction. <i>Philosophical Magazine</i> , <b>2003</b> , 83, 1255-1286	1.6	13
40	Magnetoresistance for the ferromagnetic tunnel junction with an amorphous semiconducting barrier. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	
39	Magnetic polarization of the La and Ce 5d states near the interfaces of Fe/LaHx and Fe/CeHx multilayers across the metal-insulator transition in the hydrides: An x-ray magnetic circular dichroism study. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	5
38	Interfacial scattering in magnetic multilayers and spin valves. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	16
37	Reduction of the three-dimensional Schrödinger equation for multilayered films. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	
36	Spintronics: Fundamentals and applications. <i>Reviews of Modern Physics</i> , <b>2004</b> , 76, 323-410	40.5	8168
35	Large magnetoresistance in bcc CoMgO/Co and FeCoMgO/FeCo tunnel junctions. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	271
34	Electronic structure and spin-dependent tunneling conductance under a finite bias. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	65
33	Spin Polarized Electron Tunneling. <b>2005</b> , 51-97		6
32	Self-consistent theory of scattering at disordered interfaces in layered nanostructures. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	8
31	Electron Transport in Magnetic Multilayers. <b>2005</b> , 5-50		1

30	Magnetic Tunnel Junctions Based on Half-Metallic Oxides. <b>2006</b> , 49-110		2
29	Anomalous Hall effect in disordered Fe ferromagnetic films. <i>Physical Review B</i> , <b>2006</b> , 74,	3-3	
28	Chapter One Spin-Dependent Tunneling in Magnetic Junctions. <i>Handbook of Magnetic Materials</i> , <b>2007</b> , 1-121	1-3	8
27	Tunneling spectroscopy of the Heusler compound Co <sub>2</sub> Cr <sub>0.6</sub> Fe <sub>0.1</sub> Al. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 093710	2-5	8
26	Spin-polarized tunneling between an antiferromagnet and a ferromagnet: First-principles calculations and transport theory. <i>Physical Review B</i> , <b>2007</b> , 76,	3-3	3
25	Simple models for electron and spin transport in barrier-conductor-barrier devices. <i>Solid-State Electronics</i> , <b>2007</b> , 51, 1344-1350	1-7	2
24	Tunneling magnetoresistance from a symmetry filtering effect. <i>Science and Technology of Advanced Materials</i> , <b>2008</b> , 9, 014106	7-1	87
23	Spin rotation, spin filtering, and spin transfer in directional tunneling through barriers in noncentrosymmetric semiconductors. <i>Physical Review B</i> , <b>2009</b> , 79,	3-3	15
22	Spin trajectory along an evanescent loop in zinc-blende semiconductors. <i>Physical Review B</i> , <b>2009</b> , 80,	3-3	1
21	Spin-orbit engineering of semiconductor heterostructures: A spin-sensitive quantum-phase shifter. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 082108	3-4	2
20	Creation and Control of Spin Current Using Co-Based Heusler Alloy. <i>Materia Japan</i> , <b>2010</b> , 49, 566-569	0-1	
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18	Spin Torque Oscillators and RF Currents Modulation, Locking, and Ringing. <i>Integrated Ferroelectrics</i> , <b>2011</b> , 125, 147-154	0-8	34
17	The role of interfaces in organic spin valves revealed through spectroscopic and transport measurements. <i>Physica Status Solidi (B): Basic Research</i> , <b>2012</b> , 249, 9-17	1-3	15
16	Structural defects analysis versus spin polarized tunneling in Co <sub>2</sub> FeAl/MgO/CoFe magnetic tunnel junctions with thick MgO barriers. <i>Journal of Magnetism and Magnetic Materials</i> , <b>2013</b> , 347, 79-85	2-8	9
15	Epitaxial magnetic layers grown by MBE. <b>2013</b> , 487-507		4
14	Competing Anisotropy-Tunneling Correlation of the CoFeB/MgO Perpendicular Magnetic Tunnel Junction: An Electronic Approach. <i>Scientific Reports</i> , <b>2015</b> , 5, 17169	4-9	15
13	Controlling the magnetic anisotropy in epitaxial Cr <sub>2</sub> O <sub>3</sub> clusters by an electric field. <i>Physical Review B</i> , <b>2015</b> , 91,	3-3	7

12	Superparamagnetic ground state of CoFeB/MgO magnetic tunnel junction with dual-barrier. <i>Applied Surface Science</i> , <b>2018</b> , 457, 529-535	6.7	3
11	Ab-initio study of electronic and magnetic properties of CoIrMnZ (Z = Al, Si, Ga, Ge) Heusler alloys. <i>Journal of Magnetism and Magnetic Materials</i> , <b>2020</b> , 498, 166092	2.8	2
10	Impact of single and double oxygen vacancies on electronic transport in Fe/MgO/Fe magnetic tunnel junctions. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 143902	2.5	1
9	Heusler alloys for spintronic devices: review on recent development and future perspectives. <i>Science and Technology of Advanced Materials</i> , <b>2021</b> , 22, 235-271	7.1	36
8	One- and two-dimensional electrical contacts and transport properties in monolayer black phosphorene-Ni interface. <i>Journal of Physics Condensed Matter</i> , <b>2021</b> ,	1.8	1
7	Tunnel magnetoresistance in magnetic tunnel junctions with FeAlSi electrode. <i>AIP Advances</i> , <b>2021</b> , 11, 045027	1.5	0
6	Tunneling Magnetoresistance and Interface Structure of Magnetic Tunnel Junctions with a MgO (001) Barrier. <i>Hyomen Kagaku</i> , <b>2007</b> , 28, 15-21		
5	The effect of insertion layer on the perpendicular magnetic anisotropy and its electric-field-induced change at Fe/MgO interface: a first-principles investigation. <i>Journal of Physics Condensed Matter</i> , <b>2020</b> , 32, 454001	1.8	1
4	Giant influence of clustering and anti-clustering of disordered surface roughness on electronic tunneling. <i>Chinese Physics Letters</i> ,	1.8	
3	Performance comparison of five types of TMR linear sensing units based on MgO magnetic tunnel junction. <b>2022</b> , 0		0
2	Tunnel anisotropic magnetoresistance in magnetic tunnel junctions using FeAlSi. <b>2023</b> , 13, 025005		0
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